

Hisashi Yamada

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

92 papers	1,419 citations	23 h-index	34 g-index
97 ext. papers	1,581 ext. citations	2.1 avg, IF	3.94 L-index

#	Paper	IF	Citations
92	High Brightness Blue InGaN/GaN Light Emitting Diode on Nonpolar m-plane Bulk GaN Substrate. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L960-L962	1.4	81
91	Continuous-wave Operation of AlGaIn-cladding-free Nonpolar m-Plane InGaIn/GaN Laser Diodes. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L761-L763	1.4	71
90	Thin Body III-V-Semiconductor-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors on Si Fabricated Using Direct Wafer Bonding. <i>Applied Physics Express</i> , 2009 , 2, 124501	2.4	67
89	III-V-semiconductor-on-insulator n-channel metal-insulator-semiconductor field-effect transistors with buried Al ₂ O ₃ layers and sulfur passivation: Reduction in carrier scattering at the bottom interface. <i>Applied Physics Letters</i> , 2010 , 96, 142106	3.4	58
88	Optical polarization characteristics of m-oriented InGaIn/GaN light-emitting diodes with various indium compositions in single-quantum-well structure. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 225104	3.4	52
87	High mobility CMOS technologies using III-V/Ge channels on Si platform. <i>Solid-State Electronics</i> , 2013 , 88, 2-8	1.7	51
86	Sub-10-nm Extremely Thin Body InGaAs-on-Insulator MOSFETs on Si Wafers With Ultrathin Al ₂ O ₃ Buried Oxide Layers. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1218-1220	4.4	48
85	High Electron Mobility Metal-Insulator-Semiconductor Field-Effect Transistors Fabricated on (111)-Oriented InGaAs Channels. <i>Applied Physics Express</i> , 2009 , 2, 121101	2.4	46
84	Compositional Dependence of Nonpolar m-Plane In _x Ga _{1-x} N/GaN Light Emitting Diodes. <i>Applied Physics Express</i> , 2008 , 1, 041101	2.4	46
83	Self-Aligned Metal Source/Drain In _x Ga _{1-x} As n-Metal-Oxide-Semiconductor Field-Effect Transistors Using NiInGaAs Alloy. <i>Applied Physics Express</i> , 2011 , 4, 024201	2.4	45
82	Impact of Substrate Mismatch on the Characteristic of m-plane InGaIn/GaN Light Emitting Diodes. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L1117-L1119	1.4	44
81	Comparison of InGaIn/GaN light emitting diodes grown on m-plane and a-plane bulk GaN substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 89-91	2.5	42
80	Formation of III-V-on-insulator structures on Si by direct wafer bonding. <i>Semiconductor Science and Technology</i> , 2013 , 28, 094009	1.8	36
79	Well-width dependence of optical properties of rare-earth ion-doped ZnS _{0.8} Se _{0.2} /undoped ZnS multiple quantum wells. <i>Physical Review B</i> , 2003 , 67,	3.3	34
78	Reduction in interface state density of Al ₂ O ₃ /InGaAs metal-oxide-semiconductor interfaces by InGaAs surface nitridation. <i>Journal of Applied Physics</i> , 2012 , 112, 073702	2.5	33
77	Optical polarization characteristics of InGaIn/GaN light-emitting diodes fabricated on GaN substrates oriented between (101 $\bar{0}$) and (101 $\bar{1}$) planes. <i>Applied Physics Letters</i> , 2008 , 92, 091105	3.4	33
76	Effects of piezoelectric fields on optoelectronic properties of InGaIn/GaN quantum-well light-emitting diodes prepared on nonpolar (1 $\bar{0}$ 0) and semipolar (1 $\bar{1}$ 2) orientations. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 135106	3	32

75	Extremely-thin-body InGaAs-on-insulator MOSFETs on Si fabricated by direct wafer bonding 2010 ,		30
74	Experimental Study on Electron Mobility in In _x Ga _{1-x} As-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors With In Content Modulation and MOS Interface Buffer Engineering. <i>IEEE Nanotechnology Magazine</i> , 2013 , 12, 621-628	2.6	26
73	High Performance Extremely Thin Body InGaAs-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors on Si Substrates with Ni _{1-x} Ga _x As Metal Source/Drain. <i>Applied Physics Express</i> , 2011 , 4, 114201	2.4	25
72	Impact of InGaAs surface nitridation on interface properties of InGaAs metal-oxide-semiconductor capacitors using electron cyclotron resonance plasma sputtering SiO ₂ . <i>Applied Physics Letters</i> , 2010 , 97, 132102	3.4	24
71	Optical polarization of m-plane In-GaN/GaN light-emitting diodes characterized via confocal microscope. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 1203-1206	1.6	24
70	Control of Ga-oxide interlayer growth and Ga diffusion in SiO ₂ /GaN stacks for high-quality GaN-based metal-oxide-semiconductor devices with improved gate dielectric reliability. <i>Applied Physics Express</i> , 2018 , 11, 015701	2.4	23
69	III-V/Ge High Mobility Channel Integration of InGaAs n-Channel and Ge p-Channel Metal-Oxide-Semiconductor Field-Effect Transistors with Self-Aligned Ni-Based Metal Source/Drain Using Direct Wafer Bonding. <i>Applied Physics Express</i> , 2012 , 5, 076501	2.4	23
68	Electron Mobility Enhancement of Extremely Thin Body In _{0.7} Ga _{0.3} As-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors on Si Substrates by Metal-Oxide-Semiconductor Interface Buffer Layers. <i>Applied Physics Express</i> , 2012 , 5, 014201	2.4	23
67	Effects of off-axis GaN substrates on optical properties of m-plane InGaN/GaN light-emitting diodes. <i>Journal of Crystal Growth</i> , 2008 , 310, 4968-4971	1.6	23
66	Self-aligned metal source/drain InP n-metal-oxide-semiconductor field-effect transistors using Ni _{1-x} P metallic alloy. <i>Applied Physics Letters</i> , 2011 , 98, 243501	3.4	20
65	Ultrathin Body InGaAs-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors with InP Passivation Layers on Si Substrates Fabricated by Direct Wafer Bonding. <i>Applied Physics Express</i> , 2011 , 4, 054202	2.4	18
64	Impact of La ₂ O ₃ interfacial layers on InGaAs metal-oxide-semiconductor interface properties in Al ₂ O ₃ /La ₂ O ₃ /InGaAs gate stacks deposited by atomic-layer-deposition. <i>Journal of Applied Physics</i> , 2015 , 118, 085309	2.5	17
63	Initial Processes of Atomic Layer Deposition of Al ₂ O ₃ on InGaAs: Interface Formation Mechanisms and Impact on Metal-Insulator-Semiconductor Device Performance. <i>Materials</i> , 2012 , 5, 404-414	3.5	16
62	Front-gate InGaAs-on-Insulator metal-insulator-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2010 , 97, 253502	3.4	15
61	AC response analysis of C _{IT} curves and quantitative analysis of conductance curves in Al ₂ O ₃ /InP interfaces. <i>Microelectronic Engineering</i> , 2011 , 88, 1087-1090	2.5	15
60	Enhancement mechanism of terahertz radiation from coherent longitudinal optical phonons in undoped GaAs/n-type GaAs epitaxial structures. <i>Journal of Applied Physics</i> , 2013 , 113, 143502	2.5	14
59	Electrical properties of Ni/n-GaN Schottky diodes on freestanding m-plane GaN substrates. <i>Applied Physics Express</i> , 2017 , 10, 041001	2.4	13
58	Controlled oxide interlayer for improving reliability of SiO ₂ /GaN MOS devices. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCD06	1.4	11

57	Impact of substrate off-angle on them-plane GaN Schottky diodes. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FG01	1.4	10
56	Self-aligned metal source/drain InxGa1-xAs n-MOSFETs using Ni-InGaAs alloy 2010 ,		9
55	Origin of electron mobility enhancement in (1 1 1)-oriented InGaAs channel metalinsulatorsemiconductor field-effect-transistors. <i>Microelectronic Engineering</i> , 2011 , 88, 3459-3461	2.5	8
54	Recent progress in nonpolar LEDs as polarized light emitters. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 203-205	1.6	8
53	Detection of edge component of threading dislocations in GaN by Raman spectroscopy. <i>Applied Physics Express</i> , 2018 , 11, 061002	2.4	7
52	The optical excitation mechanism in ZnS: Sm ³⁺ grown by molecular-beam epitaxy. <i>Solid State Communications</i> , 2007 , 142, 36-40	1.6	7
51	Influence of V/III Ratio of Carbon-Doped p-GaAs on Current Gain and Its Thermal Stability in InGaP/GaAs Heterojunction Bipolar Transistors. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 3909-3912	1.4	7
50	Thin metal intracavity contact and lateral current-distribution scheme for GaN-based vertical-cavity lasers. <i>Applied Physics Letters</i> , 2007 , 90, 181128	3.4	7
49	Gold particles containing plasma-polymerized styrene as an X-ray absorber. <i>Plasma Chemistry and Plasma Processing</i> , 1987 , 7, 155-167	3.6	7
48	Chemical Vapor Deposition Growth of BN Thin Films Using B ₂ H ₆ and NH ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900318	1.3	7
47	Comparison of Electrical Properties of Ni/n-GaN Schottky Diodes on c-Plane and m-Plane GaN Substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700362	1.6	7
46	Determination of edge-component Burgers vector of threading dislocations in GaN crystal by using Raman mapping. <i>Applied Physics Express</i> , 2018 , 11, 111001	2.4	7
45	High thermal stability of abrupt SiO ₂ /GaN interface with low interface state density. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FG11	1.4	6
44	Deep-level traps in lightly Si-doped n-GaN on free-standing m-oriented GaN substrates. <i>AIP Advances</i> , 2018 , 8, 045311	1.5	6
43	Characteristics of ultrafast optical responses originating from non-equilibrium carrier transport in undoped GaAs/n-type GaAs epitaxial structures. <i>Journal of Applied Physics</i> , 2013 , 113, 203506	2.5	6
42	Correlation between channel mobility improvements and negative V _{th} shifts in III-V MISFETs: Dipole fluctuation as new scattering mechanism 2010 ,		6
41	Efficient luminescence from Sm-doped ZnSSe/undoped-ZnS multi-quantum wells. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 935-938	1.6	6
40	Nondestructive visualization of threading dislocations in GaN by micro raman mapping. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCB06	1.4	5

39	Fabrication and Evaluation of N-Channel GaN Metal-Oxide-Semiconductor Field-Effect Transistors Based on Regrown and Implantation Methods. <i>Materials</i> , 2020 , 13,	3.5	5
38	High Quality Thin Body III-V-On-Insulator Channel Layer Transfer on Si Wafer Using Direct Wafer Bonding. <i>ECS Transactions</i> , 2010 , 33, 391-401	1	5
37	Evaluation of GaN substrates grown in supercritical basic ammonia. <i>Applied Physics Letters</i> , 2009 , 94, 052109	3.4	5
36	Ultrafast optical response originating from carrier-transport processes in undoped GaAs/n-type GaAs epitaxial structures. <i>Applied Physics Letters</i> , 2012 , 100, 211902	3.4	5
35	Compensation centers in ZnSeTe. <i>Journal of Applied Physics</i> , 1999 , 86, 5993-5999	2.5	5
34	Experimental Demonstration of n- and p-channel GaN-MOSFETs toward Power IC Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 015001	2	5
33	Comparative Study of Boron Precursors for Chemical Vapor-Phase Deposition-Grown Hexagonal Boron Nitride Thin Films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000241	1.6	5
32	Sulfur cleaning for (100), (111)A, and (111)B InGaAs surfaces with In content of 0.53 and 0.70 and their Al ₂ O ₃ /InGaAs MOS interface properties 2012 ,		4
31	Frequency Shift of Terahertz Electromagnetic Waves Originating from Sub-Picosecond-Range Carrier Transport in Undoped GaAs/n-Type GaAs Epitaxial Layer Structures. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 082001	1.4	4
30	High current gain stability of carbon-doped p-GaAs in InGaP/GaAs heterojunction bipolar transistors. <i>Journal of Crystal Growth</i> , 2007 , 298, 857-860	1.6	4
29	Dielectric functions of CVD-grown boron nitride from 1.1 to 9.0 eV by spectroscopic ellipsometry. <i>Applied Physics Letters</i> , 2021 , 118, 112101	3.4	4
28	Energy band structure and electrical properties of Ga-oxide/GaN interface formed by remote oxygen plasma. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 06KA05	1.4	4
27	High mobility III-V-on-insulator MOSFETs on Si with ALD-Al ₂ O ₃ BOX layers 2010 ,		3
26	Fabrication of submicron active-region-buried GaN hexagonal frustum structures by selective area growth for directional micro-LEDs. <i>Journal of Crystal Growth</i> , 2019 , 507, 437-441	1.6	3
25	Behavior of Threading Dislocations from GaN Substrate to Epitaxial Layer. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900527	1.3	2
24	Interface properties of SiO ₂ /GaN structures formed by chemical vapor deposition with remote oxygen plasma mixed with Ar or He. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 06KA01	1.4	2
23	Impact of remote plasma oxidation of a GaN surface on photoluminescence properties. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SEEC02	1.4	2
22	Simple strategy for enhancing terahertz emission from coherent longitudinal optical phonons using undoped GaAs/n-type GaAs epitaxial layer structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 343-345		2

21	Relationships between Interface Structures and Electrical Properties in the High-k/III-V System. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1194, 68		2
20	On the mechanisms limiting mobility in InP/InGaAs buried channel nMISFETs. <i>Microelectronic Engineering</i> , 2011 , 88, 1076-1078	2.5	2
19	Controlling Anion Composition at Metal/Insulator/Semiconductor Interfaces on III-V Channels by Plasma Processing. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 065701	1.4	2
18	The Effect of n-GaAs Carrier Concentration on Current Gain in InGaP/GaAs Heterojunction Bipolar Transistors. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 5122-5124	1.4	2
17	Quenching mechanism of luminescence in Sm-doped ZnS. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 954-957	2.5	2
16	Controlling Anion Composition at Metal/Insulator/Semiconductor Interfaces on III-V Channels by Plasma Processing. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 065701	1.4	2
15	Growth Temperature Effects of Chemical Vapor Deposition-Grown Boron Nitride Layer Using B ₂ H ₆ and NH ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900521	1.3	2
14	Low-temperature formation of Ga-oxide/GaN interface with remote oxygen plasma and its interface properties. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 06JE01	1.4	2
13	Ferroelectrics field modulation imaging: A useful technique for domain and domain-wall observations. <i>Ferroelectrics</i> , 2020 , 556, 37-43	0.6	1
12	(Invited) III-V-On-Insulator MOSFETs on Si Substrates Fabricated by Direct Bonding Technique. <i>ECS Transactions</i> , 2010 , 33, 359-370	1	1
11	Customized Filter Cube in Fluorescence Microscope Measurements of InGaN/GaN Quantum-Well Characterization. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 098003	1.4	1
10	Si-related defects in InGaP/GaAs heterojunction bipolar transistors. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 44-47	2.8	1
9	Analysis of dislocation line tilt in GaN single crystal by Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SAAD03	1.4	1
8	Impact of gate electrode formation process on Al ₂ O ₃ /GaN interface properties and channel mobility. <i>Applied Physics Express</i> , 2021 , 14, 081001	2.4	0
7	Reduction in residual impurities in semi-polar 30° and 20° GaN grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2019 , 512, 119-123	1.6	
6	Formation and reduction of pyramidal hillocks on InGaAs/InP(111)A. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 644-647	1.3	
5	Comparative study of photoluminescence properties obtained from SiO ₂ /GaN and Al ₂ O ₃ /GaN structures. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SIIB22	1.4	
4	Time Evolution of Terahertz Electromagnetic Waves from Undoped GaAs/n-type GaAs Epitaxial Layer Structures Clarified with Use of a Time-Partitioning Fourier Transform Method. <i>Physics Procedia</i> , 2012 , 29, 30-35		

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| 3 | Frequency-tunable terahertz electromagnetic wave emitters based on undoped GaAs/n-type GaAs epitaxial layer structures utilizing sub-picosecond-range carrier-transport processes. <i>Journal of Luminescence</i> , 2011 , 131, 531-534 | 3.8 |
| 2 | Hydrogen-related defects in InGaP/GaAs heterojunction bipolar transistors. <i>Journal of Crystal Growth</i> , 2008 , 310, 5223-5226 | 1.6 |
| 1 | Fabrication and analysis of InAlN/GaN metal-insulator-semiconductor high-electron-mobility transistors based on AlN/GaN superlattice channel. <i>Applied Physics Letters</i> , 2021 , 119, 143503 | 3.4 |